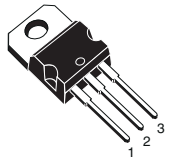
STP70NS04ZC

N-channel clamped 8mΩ - 80A TO-220
Fully protected SAFeFET™ Power MOSFET

Features

Type	V_{DSS}	$R_{DS(on)}$	I_D
STP70NS04ZC	Clamped	< 10mΩ	80A

- Low capacitance and gate charge
- 100% avalanche tested
- 175°C maximum junction temperature



TO-220

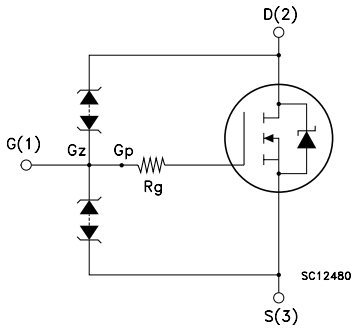
Description

This fully clamped Power MOSFET is produced by using the latest advanced company's Mesh OVERLAY process which is based on a novel strip layout. The inherent benefits of the new technology coupled with the extra clamping capabilities make this product particularly suitable for the harshest operation conditions such as those encountered in the automotive environment. Any other application requiring extra ruggedness is also recommended.

Applications

- Switching applications
  - ABS, solenoid drivers
  - Motor control
  - Dc-dc converters

Internal schematic diagram



Order code

Part number	Marking	Package	Packaging
STP70NS04ZC	P70NS04ZC	TO-220	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	33 (1)	V
V_{DG}	drain-gate voltage	33 (1)	V
V_{GS}	Gate-source voltage	±20 (1)	V
I_D (2)	Drain current (continuous) at T_C = 25°C	80	A
I_D (2)	Drain current (continuous) at T_C=100°C	63	A
I_{DG}	Drain gate current (continuous)	±50	A
I_{GS}	Gate-source current (continuous)	±50	A
I_{DM} (3)	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at T_C = 25°C	180	W
	Derating factor	1.2	W/°C
$V_{ESD(G-S)}$	Gate-source ESD (HBM-C=100pF, R=1.5KΩ)	± 8	kV
$V_{ESD(G-D)}$	Gate-drain ESD (HBM-C=100pF, R=1.5KΩ)	± 8	kV
$V_{ESD(D-S)}$	Drain-source ESD (HBM-C=100pF, R=1.5KΩ)	± 8	kV
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 175	°C

1. Voltage is limited by zener diodes
2. Current limited by wire bonding
3. Pulse width limited by safe operating area

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.83	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	°C/W
T_l	Maximum lead temperature for soldering purpose	300	°C

Table 3. Avalanche data

Symbol	Parameter	Value	Unit
I_{AS}	Avalanche current, repetitive or not repetitive (pulse width limited by Tjmax)	30	A
E_{AS}	Single pulse avalanche energy (starting Tj=25°C, I_D=I_{AS}, V_{DD}=50V)	720	mJ

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DG}$	Clamped voltage	I_D = 1mA, V_{GS}= 0	33			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 16V			1	µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±10V			2	µA
V_{GSS}	Gate-source breakdown voltage	I_{GS} =±100µA	18			V
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 1mA	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10V, I_D= 40A		8	11	mΩ

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} =15V, I_D = 30A		35		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} =25V, f=1 MHz, V_{GS}=0		1930 700 230		pF pF pF
$t_{r(Voff)}$ t_f t_c	Off voltage rise time Fall time Cross-over time	V_{CLAMP}=32V, I_D=60A, V_{GS}=10V, R_G=4.7Ω		110 90 140		ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD}=32V, I_D = 60A V_{GS} =10V		58 14 26		nC nC nC
R_G	Internal gate resistor			14		Ω

1. Pulsed: pulse duration=300µs, duty cycle 1.5%

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(1)	Source-drain current Source-drain current (pulsed)				80 320	A A
V_{SD}(2)	Forward on voltage	I_{SD}=80A, V_{GS}=0			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=80A, di/dt = 100A/µs, V_{DD}= 30 V, Tj=150°C		90 0.18 4		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

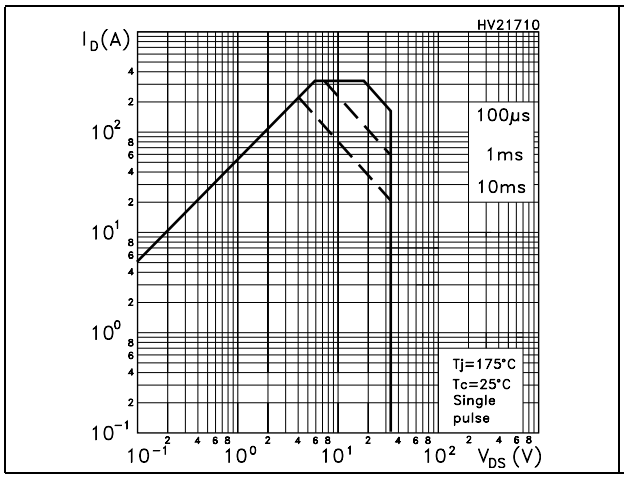


Figure 2. Thermal impedance

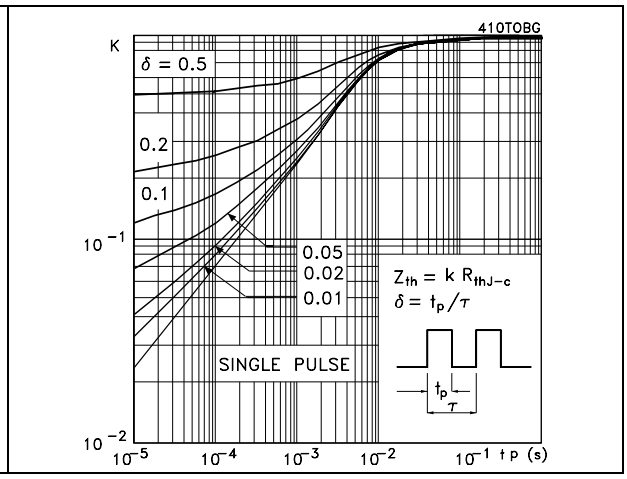


Figure 3. Output characteristics

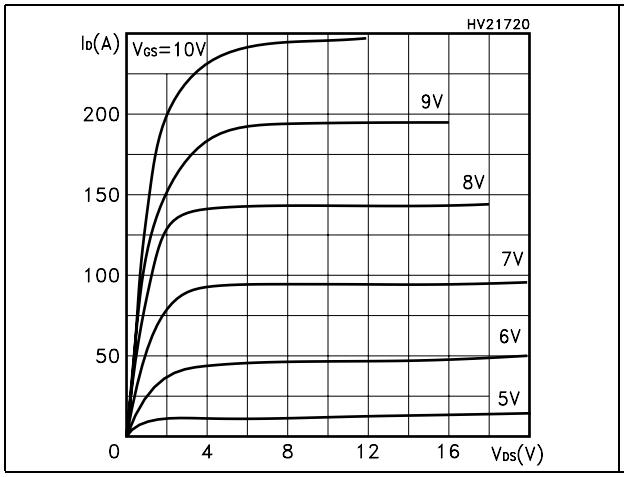


Figure 4. Transfer characteristics

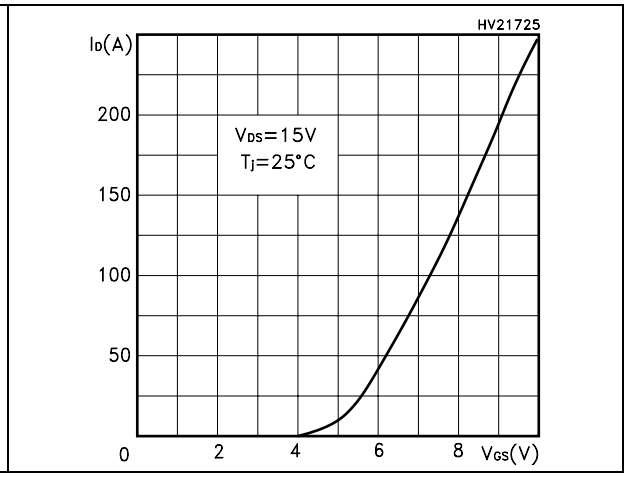


Figure 5. Transconductance

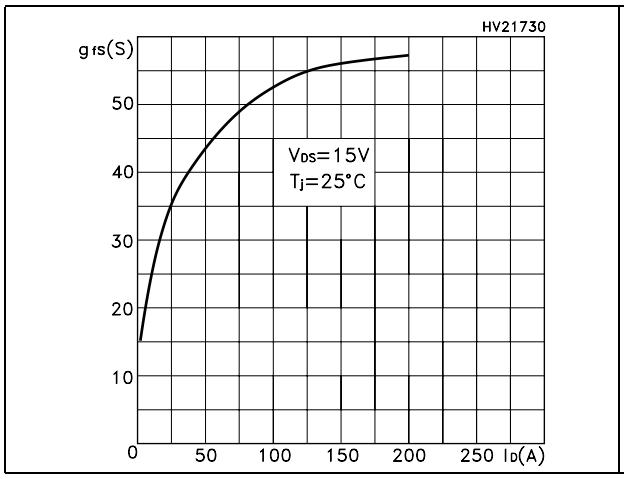


Figure 6. Static drain-source on resistance